### **NSR2030QMUTWG**

## 2A, 30V Schottky Full Bridge

These full bridge Schottky barrier diodes are designed for the rectification of the high speed signal of wireless charging. The NSR2030QMUTWG has a very low forward voltage that will reduce conduction loss. It is housed in a UDFN 3.5 x 3.5 x 0.5 mm package that is ideal for space constrained wireless applications.

#### **Features**

- Extremely Fast Switching Speed
- Low Forward Voltage -0.54 V (Typ) @  $I_F = 2 \text{ A}$
- These Devices are Pb-Free, Halogen Free and are RoHS Compliant

#### **Typical Applications**

• Low Voltage Full Bridge Rectification & Wireless Charging

#### MAXIMUM RATINGS (T<sub>J</sub> = 125°C unless otherwise noted) (Note 1)

Rating	Symbol	Value	Unit
Reverse Voltage	$V_R$	30	V
Forward Current (DC)	Ιϝ	2.0	Α
Forward Current Surge Peak (60 Hz, 1 cycle)	I <sub>FSM</sub>	12.5	А
Non-Repetitive Peak Forward Current (Square Wave, $T_J = 25^{\circ}C$ prior to surge) $t = 1 \mu s$ t = 1 ms t = 1 s	I <sub>FSM</sub>	40 10 3.0	A

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

## 1. All specifications pertain to a single diode. **THERMAL CHARACTERISTICS**

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board T <sub>A</sub> = 25°C	P <sub>D</sub> (Note 2)	2.08	W
Derate above 25°C		20.8	mW/°C
Thermal Resistance Junction to Ambient	R <sub>θJA</sub> (Note 2)	48	°C/W
Total Device Dissipation FR-5 Board $T_A = 25$ °C	P <sub>D</sub> (Note 3)	0.75	W
Derate above 25°C		7.6	mW/°C
Thermal Resistance Junction to Ambient	R <sub>θJA</sub> (Note 3)	132	°C/W
Total Device Dissipation FR-5 Board T <sub>A</sub> = 25°C	P <sub>D</sub> (Note 4)	0.87	W
Derate above 25°C		8.8	mW/°C
Thermal Resistance Junction to Ambient	R <sub>θJA</sub> (Note 4)	114	°C/W
Junction Temperature	TJ	+125	°C
Storage Temperature Range	T <sub>stg</sub>	-55 to +150	°C

- 2. 4 Layer JEDEC JESD51.7 FR-4 @ 10 mm<sup>2</sup>, 1 oz. copper trace, still air.
- 3. Single Layer JEDEC JESD51.3 FR-4 @ 100 mm<sup>2</sup>, 1 oz. copper trace, still air.
- 4. Single Layer JEDEC JESD51.3 FR-4 @ 100 mm<sup>2</sup>, 2 oz. copper trace, still air.



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#### MARKING DIAGRAM



UDFN4 3.5x3.5 CASE 517DA

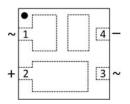


2030 = Specific Device Code A = Assembly Location

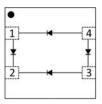
Y = Year WW = Work Week ■ Pb-Free Package

(Note: Microdot may be in either location)

#### **PIN CONNECTIONS**



#### **DEVICE SCHEMATIC**



#### **ORDERING INFORMATION**

Device	Package	Shipping†
NSR2030QMUTWG	UDFN4 (Pb-Free)	3000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

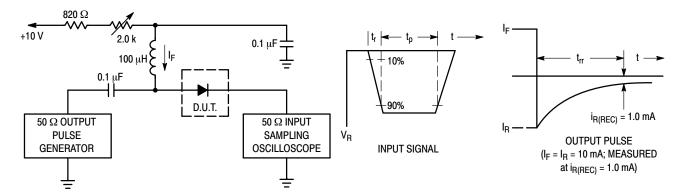
#### **NSR2030QMUTWG**

**ELECTRICAL CHARACTERISTICS** (T<sub>A</sub> = 25°C unless otherwise noted) (Note 5)

Characteristic	Symbol	Min	Тур	Max	Unit
Reverse Breakdown Voltage (I <sub>R</sub> = 1.0 mA)	V <sub>(BR)</sub>	30	_	-	V
Reverse Leakage (V <sub>R</sub> = 30 V)	I <sub>R</sub>	-	5.0	20	μΑ
Forward Voltage (I <sub>F</sub> = 0.5 A)	V <sub>F</sub>	-	0.41	0.455	V
Forward Voltage (I <sub>F</sub> = 1.0 A)	V <sub>F</sub>	-	0.46	0.55	V
Forward Voltage (I <sub>F</sub> = 2.0 A)	V <sub>F</sub>	-	0.54	0.65	V
Reverse Recovery Time $(I_F = I_R = 10 \text{ mA}, I_{R(REC)} = 1.0 \text{ mA})$	t <sub>rr</sub>	-	34	-	ns
Input Capacitance (pins 1 to 3) (V <sub>R</sub> = 1.0 V, f = 1.0 MHz)	C <sub>T</sub>	-	102	-	pF

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

5. All specifications pertain to a single diode.



Notes: 1. A 2.0 k $\Omega$  variable resistor adjusted for a Forward Current (I<sub>F</sub>) of 10 mA.

2. Input pulse is adjusted so  $I_{R(peak)}$  is equal to 10 mA.

3.  $t_p \gg t_{rr}$ 

Figure 1. Recovery Time Equivalent Test Circuit

#### **NSR2030QMUTWG**

#### TYPICAL CHARACTERISTICS

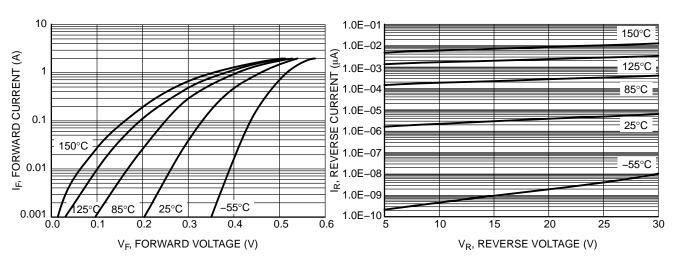


Figure 1. Forward Voltage

Figure 2. Reverse Leakage

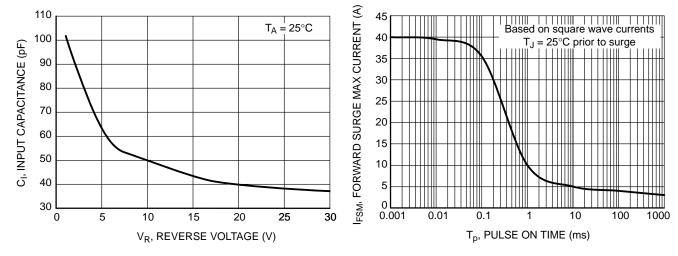


Figure 3. Input Capacitance

Figure 4. Forward Surge Current

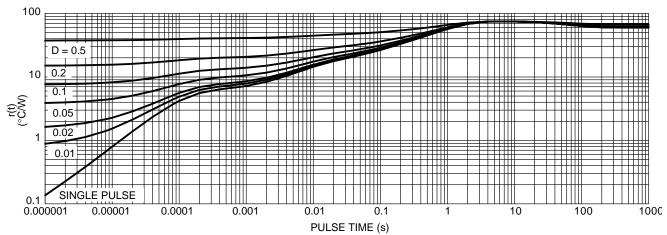
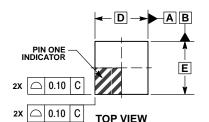


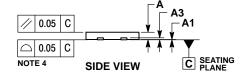
Figure 5. Thermal Response

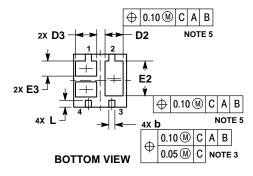


#### UDFN4 3.5x3.5, 1.55P CASE 517DA **ISSUE A**

**DATE 25 SEP 2014** 

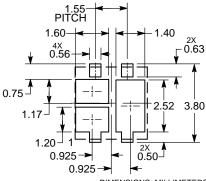






# G e/2 SUPPLEMENTAL BOTTOM VIEW

#### **RECOMMENDED SOLDERING FOOTPRINT\***



**DIMENSIONS: MILLIMETERS** 

#### NOTES:

- NOTES:

  1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.

  2. CONTROLLING DIMENSION: MILLIMETERS.

  3. DIMENSION & APPLIES TO PLATED TERMINAL AND IS MEASURED BETWEEN 0.05 AND 0.15 MM FROM THE TERMINAL TIP.

  4. COPLANARITY APPLIES TO THE EXPOSED PADS AS WELL AS THE TERMINALS.

  5. POSITIONAL TOLERANCE APPLIES TO ALL OF THE FXPOSED PADS.
- OF THE EXPOSED PADS.

	MILLIMETERS		
DIM	MIN	MAX	
Α	0.45	0.55	
A1	0.00	0.05	
A3	0.13 REF		
b	0.35	0.45	
D	3.50 BSC		
D2	1.15	1.25	
D3	1.35	1.45	
Е	3.50 BSC		
E2	2.25	2.35	
E3	0.95	1.05	
е	1.55 BSC		
F	0.925 BSC		
G	0.58 BSC		
L	0.35	0.55	

#### **GENERIC MARKING DIAGRAM\***



XXXX = Specific Device Code

= Assembly Location Α

= Year

= Work Week WW

= Pb-Free Package

(Note: Microdot may be in either location)

\*This information is generic. Please refer to device data sheet for actual part mark-

Pb-Free indicator, "G" or microdot " ■", may or may not be present.

DOCUMENT NUMBER:	98AON91404F
STATUS:	ON SEMICONDUCTOR STANDARD
NEW STANDARD:	
DESCRIPTION:	UDFN4 3.5X3.5, 1.55P

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<sup>\*</sup>For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.



DOCUMENT	NUMBER:
98AON91404	ŀF

PAGE 2 OF 2

ICCLIE	DEVICION	DATE
ISSUE	REVISION	DATE
0	RELEASED FOR PRODUCTION. REQ. BY D. TRUHITTE.	24 SEP 2014
Α	CORRECTED GENERIC MARKING DIAGRAM INFORMATION. REQ. BY D. TRUHITTE.	25 SEP 2014

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